8. (Amended) A multi-layer electrode for an integrated circuit, comprising:

a conductive barrier layer;

a first conductive liner deposited over the conductive barrier layer, the first conductive liner comprising a molecular grain structure having a plurality of columns;

a second conductive liner deposited over the first conductive liner, the second conductive liner comprising a conductive oxide; and

a conductive layer deposited on the second conductive liner, the conductive layer comprising a molecular grain structure having a plurality of columns, wherein the columns of the conductive layer are not aligned with the columns of the first conductive liner.

25. (New) The multi-layer electrode according to Claim 1, wherein the second conductive liner comprises a thickness such that the second conductive liner is etchable by the same etchant gas used to etch the first conductive liner and the conductive layer.

26. (New) The multi-layer electrode according to Claim 1, wherein the conductive layer comprises a molecular grain structure having columns, the conductive layer including a top surface; wherein the first conductive liner comprises a molecular grain structure having columns; wherein the columns of the conductive layer are not aligned with the columns of the first conductive liner; and wherein the second conductive liner prevents diffusion of oxide from the conductive layer top surface through the conductive layer to the conductive barrier layer.

27. (New) The multi-layer electrode according to Claim 8, wherein the second conductive liner comprises a thickness such that the second conductive liner is etchable by the same etchant gas used to etch the first conductive liner and the conductive layer.

28. (New) An electrode for a semiconductor device, comprising:

a conductive barrier layer;

a platinum liner formed over the conductive barrier layer, the platinum liner comprising a molecular grain structure having a plurality of columns;

a conductive oxide formed over the platinum liner, the conductive oxide having a thickness of 20-50 Angstroms; and

a platinum layer formed over the conductive oxide, the platinum layer comprising a molecular grain structure having a plurality of columns, wherein the columns of the platinum layer are not aligned with the columns of the platinum liner.

29. (New) The multi-layer electrode according to Claim 28 wherein the second conductive liner comprises IrO_2 or RuO_2.

30. (New) A multi-layer electrode for an integrated circuit, comprising:

a conductive barrier layer;

a first conductive liner deposited over the conductive barrier layer;

a second conductive liner deposited over the first conductive liner, the second conductive liner comprising a conductive oxide, the second conductive liner having a thickness of 20-50 Angstroms; and

a conductive layer deposited on the second conductive liner.

In the specification:

Please replace the paragraph beginning on page 10, line 6, with the following:

A layer of conductive material 344 is deposited over the second conductive liner 342. Conductive layer 344 preferably comprises Pt, and may alternatively comprise other conductive materials such as Ir, Ru, Pd or combinations thereof, for example. Preferably, conductive material 344 comprises 1500-3500 Angstroms of Pt, and more preferably comprises 2200 Angstroms of Pt.

REMARKS

Claims 1-13 and 21-30 are pending in the present application. Claim 8 and the specification are amended herein. Claims 25-30 are added herein. The Applicants respectfully request